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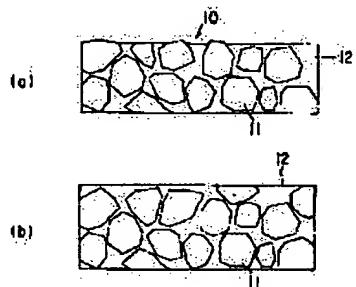
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(21) Application number : 11-267207 (71) Applicant : TOSHIBA CORP
 (22) Date of filing : 21.09.1999 (72) Inventor : SUGURO KYOICHI
 MATSUO KOJI
 NAKAMURA SHINICHI

(54) SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME

(57) Abstract:

PROBLEM TO BE SOLVED: To improve the insulating performance of an insulating film.
 SOLUTION: An insulating film 10, formed on the main face side of a semiconductor substrate, is constituted of plural grain-shaped insulating regions 11 made of metallic oxide and an inter-grain insulating region 12 made of amorphous insulating insulators formed among the adjacent grain-shaped insulating regions.



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